

MEDIUM-POWER PNP TRANSISTORS

...ideal for use as drivers, switches and medium- power amplifier and applications

FEATURES:

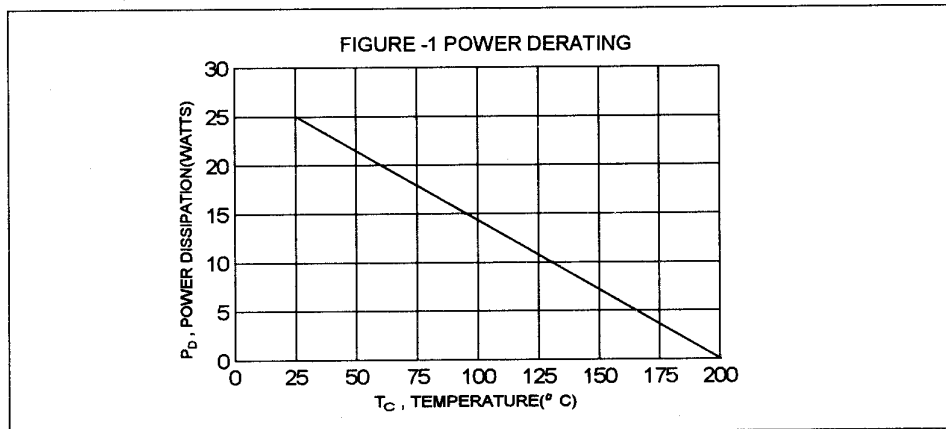
- * Low Collector-Emitter Saturation Voltage -
 $V_{CE(SAT)} = 0.6V(\text{Max.}) @ I_C = 1.0A$
- * High Gain Characteristics -
 $hFE = 30 \sim 100 @ I_C = 250mA$
- * Excellent Safe Area Limits

MAXIMUM RATINGS

Characteristic	Symbol	2N3740	2N3741	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	V
Collector-Base Voltage	V_{CBO}	60	80	V
Emitter-Base Voltage	V_{EBO}	7.0		V
Collector Current-Continuous -Peak	I_C I_{CM}	4.0 10		A
Base Current	I_B	2.0		A
Total Power Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	25 0.143		W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +200		$^\circ C$

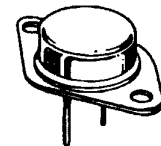
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	7.0	$^\circ C/W$

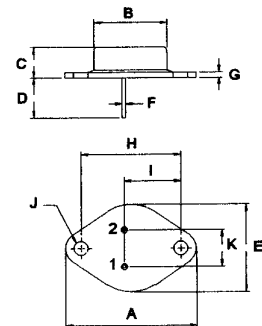


PNP
2N3740
2N3741

4 AMPERE
POWER TRANSISTORS
PNP SILICON
60 - 80 Volts
25 Watts



TO-66



PIN 1. BASE
2. EMITTER
COLLECTOR (CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	30.60	32.52
B	13.85	14.16
C	6.54	7.22
D	9.50	10.50
E	17.26	18.46
F	0.76	0.92
G	1.38	1.65
H	24.16	24.78
I	13.84	15.60
J	3.32	3.92
K	4.86	5.34

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (1) ($I_C = 100\text{ mA}$, $I_B = 0$)	2N3740 2N3741	$V_{CE(SUS)}$	60 80	V
Collector Cutoff Current ($V_{CE} = 40\text{ V}$, $I_B = 0$) ($V_{CE} = 60\text{ V}$, $I_B = 0$)	2N3740 2N3741	I_{CEO}	1.0 1.0	mA
Collector Cutoff Current ($V_{CE} = 60\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$) ($V_{CE} = 80\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$) ($V_{CE} = 40\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$, $T_c = 150^\circ\text{C}$) ($V_{CE} = 60\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$, $T_c = 150^\circ\text{C}$)	2N3740 2N3741 2N3740 2N3741	I_{CEX}	100 100 1.0 1.0	μA μA mA mA
Collector Cutoff Current ($V_{CB} = 60\text{ V}$, $I_E = 0$) ($V_{CB} = 80\text{ V}$, $I_E = 0$)	2N3740 2N3741	I_{CBO}	100 100	μA
Emitter Cutoff Current ($V_{EB} = 7.0\text{ V}$, $I_C = 0$)		I_{EBO}	0.5	mA

ON CHARACTERISTICS (1)

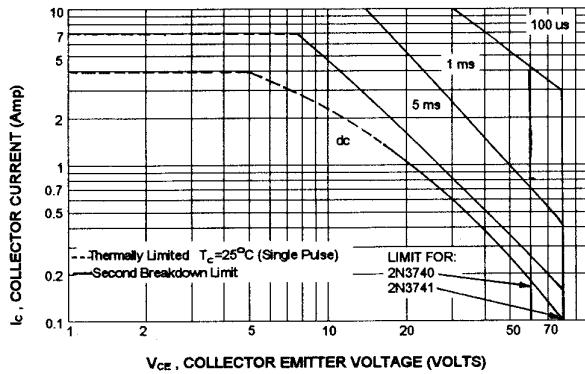
DC Current Gain ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ V}$) ($I_C = 250\text{ mA}$, $V_{CE} = 1.0\text{ V}$) ($I_C = 500\text{ mA}$, $V_{CE} = 1.0\text{ V}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 1.0\text{ V}$)		hFE	40 30 20 10	100
Collector-Emitter On Voltage ($I_C = 1.0\text{ A}$, $I_B = 125\text{ mA}$)		$V_{CE(sat)}$		0.6
Base-Emitter On Voltage ($I_C = 250\text{ mA}$, $V_{CE} = 1.0\text{ V}$)		$V_{BE(on)}$		1.0

DYNAMIC CHARACTERISTICS

Current-Gain-Bandwidth Product (2) ($I_C = 100\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ MHz}$)		f_T	3.0	MHz
Common Base Output Capacitance ($V_{CB} = 10\text{ V}$, $I_C = 0$, $f = 100\text{ KHz}$)		C_{ob}		100
Small-Signal Current Gain ($I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ KHz}$)		h_{fe}	25	

(1) Pulse Test: Pulse width $\leq 300\text{ us}$, Duty Cycle $\leq 2.0\%$ (2) $f_T = |h_{fe}| \cdot f_{test}$

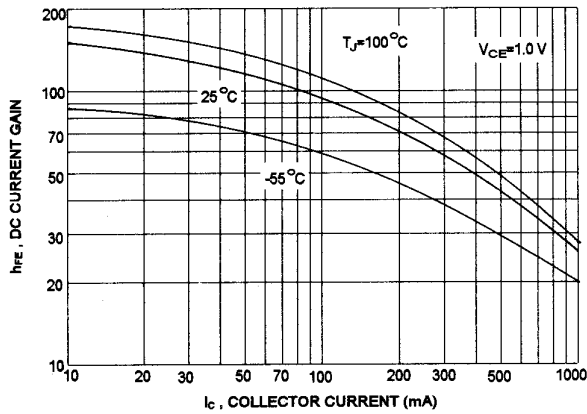
ACTIVE-REGION SAFE OPERATING AREA (SOA)



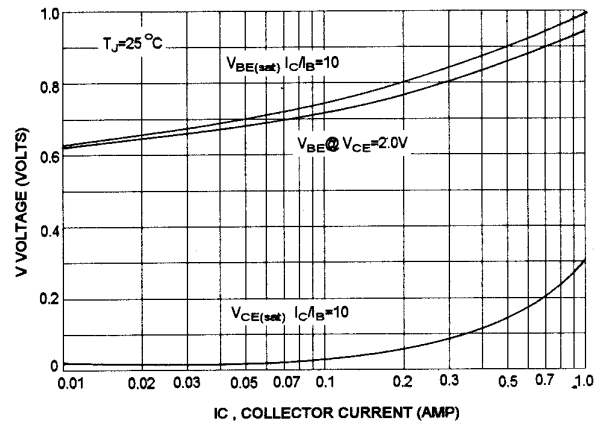
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)}=200^\circ\text{C}$; T_c is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 200^\circ\text{C}$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown

DC CURRENT GAIN



"ON" VOLTAGES



COLLECTOR SATURATION REGION

